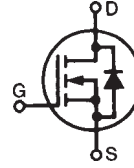


TrenchHV™ Power MOSFET

IXTA56N15T
IXTP56N15T

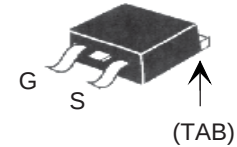
$$\begin{aligned} V_{DSS} &= 150 \text{ V} \\ I_{D25} &= 56 \text{ A} \\ R_{DS(on)} &\leq 36 \text{ m}\Omega \end{aligned}$$

N-Channel Enhancement Mode
Avalanche Rated

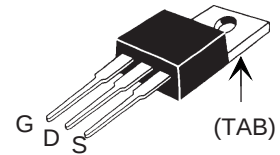


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 175°C	150	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 175°C ; $R_{GS} = 1 \text{ M}\Omega$	150	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	56	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	140	A
I_{AR}	$T_C = 25^\circ\text{C}$	5	A
E_{AS}	$T_C = 25^\circ\text{C}$	500	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$ $T_J \leq 175^\circ\text{C}$, $R_G = 5 \Omega$	3	V/ns
P_D	$T_C = 25^\circ\text{C}$	300	W
T_J		-55 ... +175	$^\circ\text{C}$
T_{JM}		175	$^\circ\text{C}$
T_{stg}		-55 ... +175	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
T_{SOLD}	Plastic body for 10 seconds	260	$^\circ\text{C}$
M_d	Mounting torque (TO-220)	1.13 / 10	Nm/lb.in.
Weight	TO-220	3	g
	TO-263	2.5	g

TO-263 (IXTA)



TO-220 (IXTP)



G = Gate D = Drain
S = Source TAB = Drain

Features

- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- easy to drive and to protect
- 175 °C Operating Temperature

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	150		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$			$\pm 100 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$			5 μA
	$V_{GS} = 0 \text{ V}$ $T_J = 150^\circ\text{C}$			200 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 28 \text{ A}$, Notes 1, 2			36 m Ω

Symbol	Test Conditions	Characteristic Values		
(T _J = 25°C unless otherwise specified)		Min.	Typ.	Max.
g _{fs}	V _{DS} = 10 V; I _D = 28 A, Note 1	23	39	S
C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		2250	pF
C _{oss}			330	pF
C _{rss}			50	pF
t _{d(on)}	Resistive Switching Times		16	ns
t _r	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 28 A		17	ns
t _{d(off)}	R _G = 5 Ω (External)		43	ns
t _f			18	ns
Q _{g(on)}	V _{GS} = 10 V, V _{DS} = 0.5 V _{DSS} , I _D = 25 A		34	nC
Q _{gs}			10	nC
Q _{gd}			11	nC
R _{thJC}	TO-220	0.50		0.50 °C/W
R _{thCH}				°C/W

Source-Drain Diode

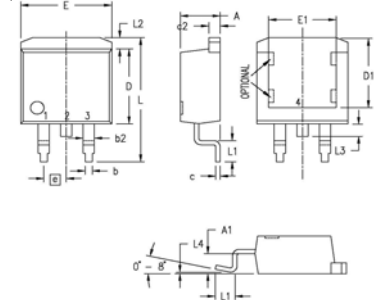
Symbol	Test Conditions	Characteristic Values		
(T _J = 25°C unless otherwise specified)		Min.	Typ.	Max.
I _S	V _{GS} = 0 V			56 A
I _{SM}	Pulse width limited by T _{JM}			160 A
V _{SD}	I _F = 25 A, V _{GS} = 0 V, Note 1			1.1 V
t _{rr}	I _F = 25 A, -di/dt = 100 A/μs V _R = 50 V, V _{GS} = 0 V		100	ns

- Notes: 1. Pulse test, t ≤ 300 μs, duty cycle, d ≤ 2 %;
2. On through-hole packages, R_{DS(on)} Kelvin test contact location must be 5 mm or less from the package body.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

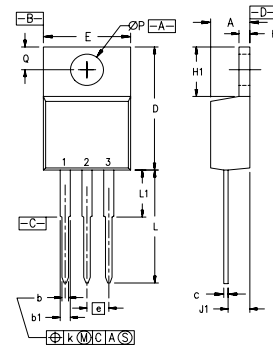
TO-263 (IXTA) Outline



Pins: 1 - Gate 2 - Drain
3 - Source 4, TAB - Drain

Dim.	Millimeter	Inches
	Min. Max.	Min. Max.
A	4.06 4.83	.160 .190
A1	2.03 2.79	.080 .110
b	0.51 0.99	.020 .039
b2	1.14 1.40	.045 .055
c	0.46 0.74	.018 .029
c2	1.14 1.40	.045 .055
D	8.64 9.65	.340 .380
D1	7.11 8.13	.280 .320
E	9.65 10.29	.380 .405
E1	6.86 8.13	.270 .320
e	2.54 BSC	.100 BSC
L	14.61 15.88	.575 .625
L1	2.29 2.79	.090 .110
L2	1.02 1.40	.040 .055
L3	1.27 1.78	.050 .070
L4	0 0.38	0 .015
R	0.46 0.74	.018 .029

TO-220 (IXTP) Outline



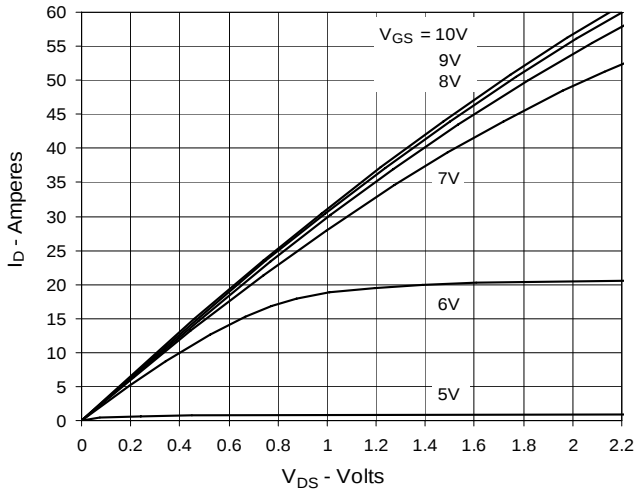
Pins: 1 - Gate 2 - Drain
3 - Source 4, TAB - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100	BSC	2.54	BSC
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

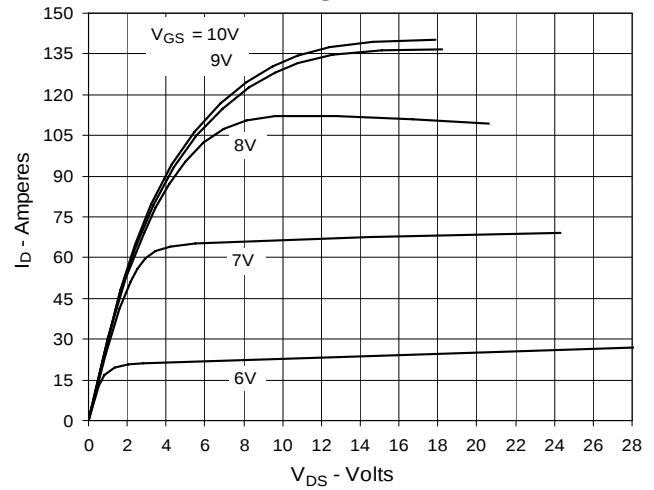
IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338 B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

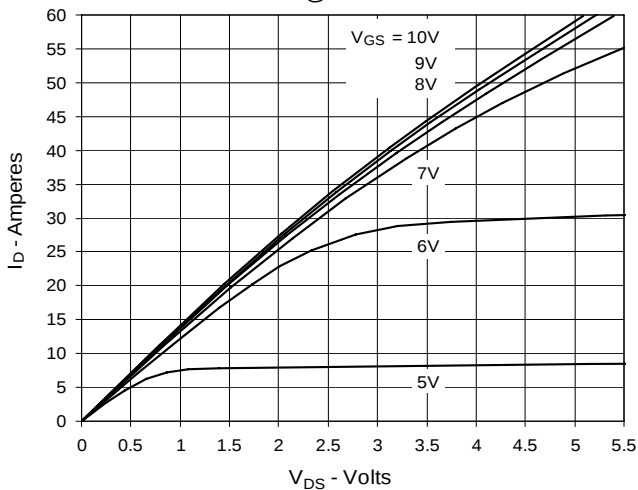
**Fig. 1. Output Characteristics
@ 25°C**



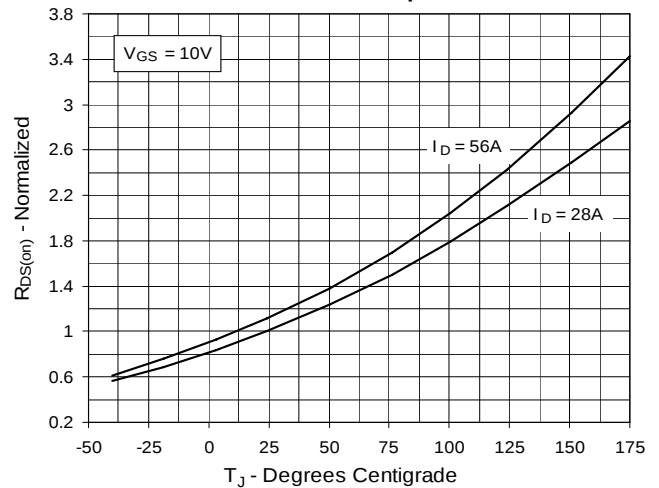
**Fig. 2. Extended Output Characteristics
@ 25°C**



**Fig. 3. Output Characteristics
@ 150°C**



**Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 28A$ Value
vs. Junction Temperature**



**Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 28A$ Value
vs. Drain Current**

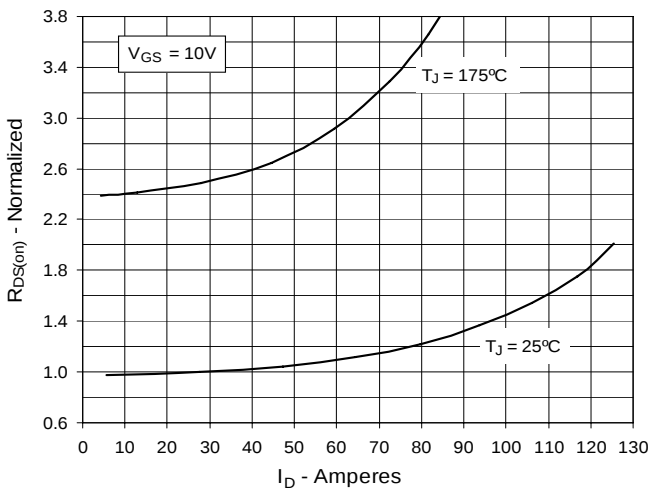


Fig. 6. Drain Current vs. Case Temperature

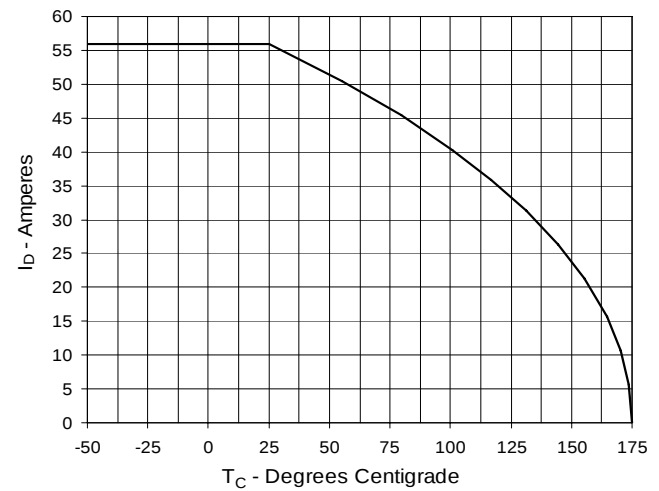


Fig. 7. Input Admittance

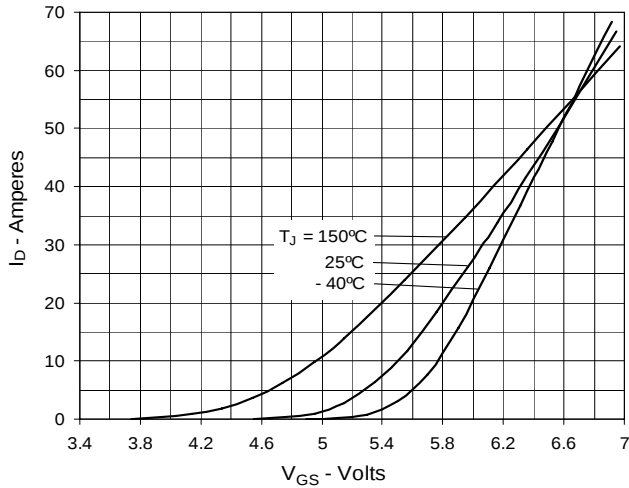


Fig. 8. Transconductance

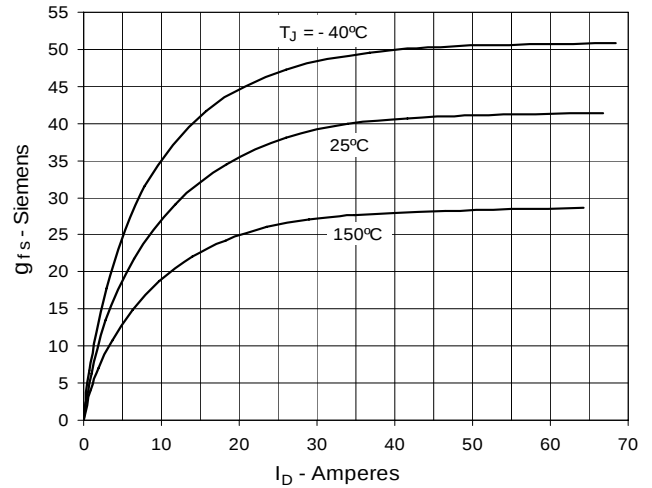


Fig. 9. Forward Voltage Drop of Intrinsic Diode

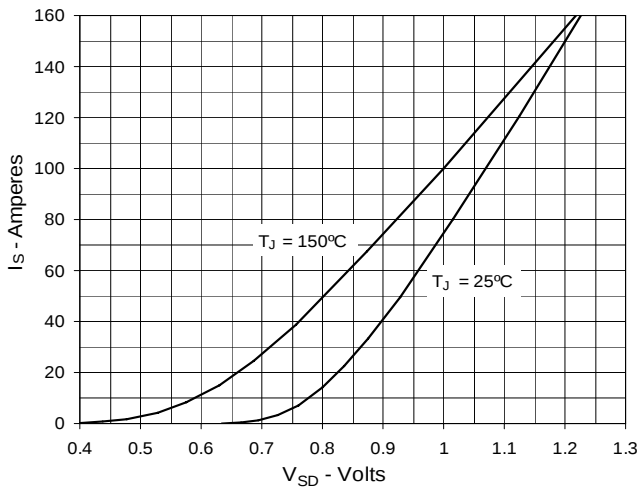


Fig. 10. Gate Charge

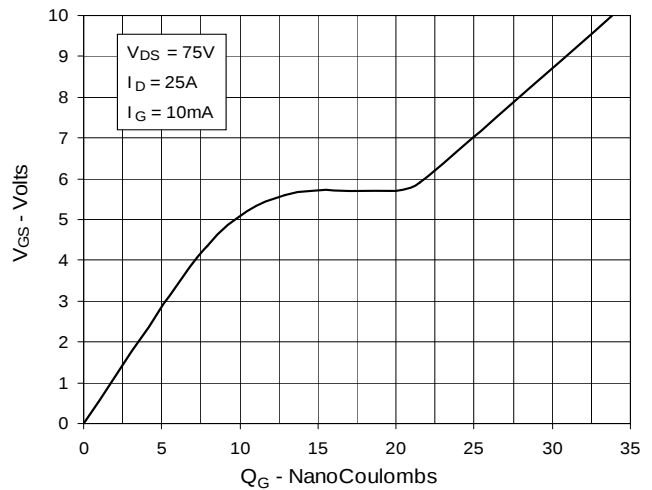


Fig. 11. Capacitance

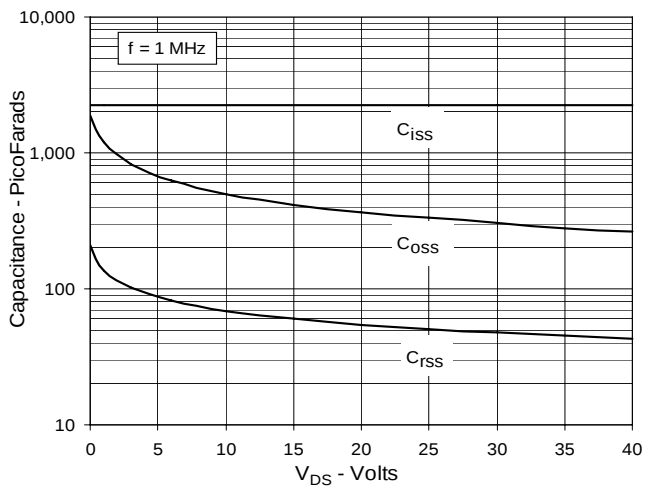


Fig. 12. Maximum Transient Thermal Impedance

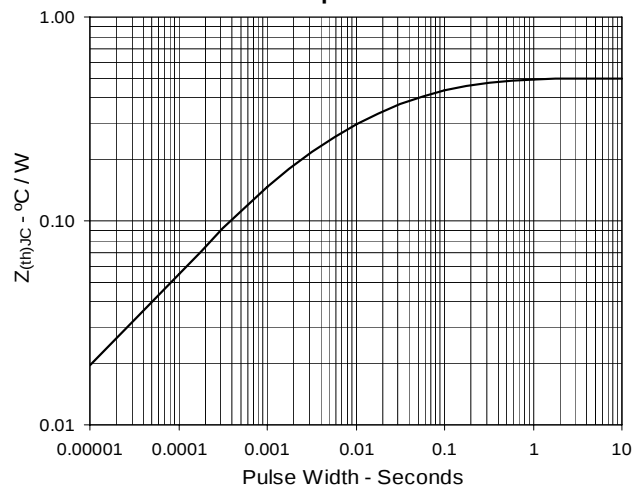


Fig. 13. Resistive Turn-on
Rise Time vs. Junction Temperature

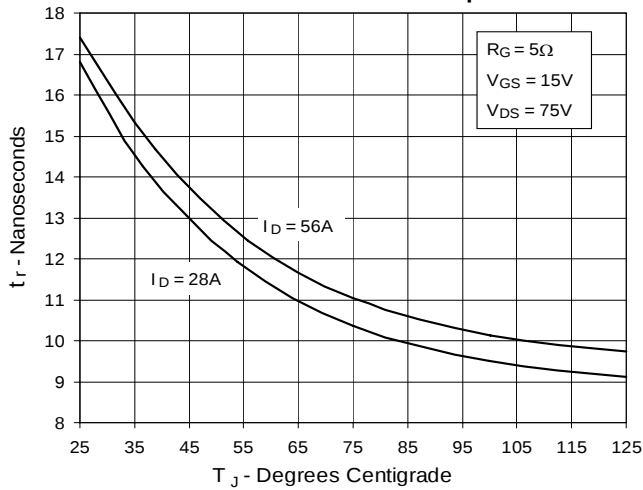


Fig. 14. Resistive Turn-on
Rise Time vs. Drain Current

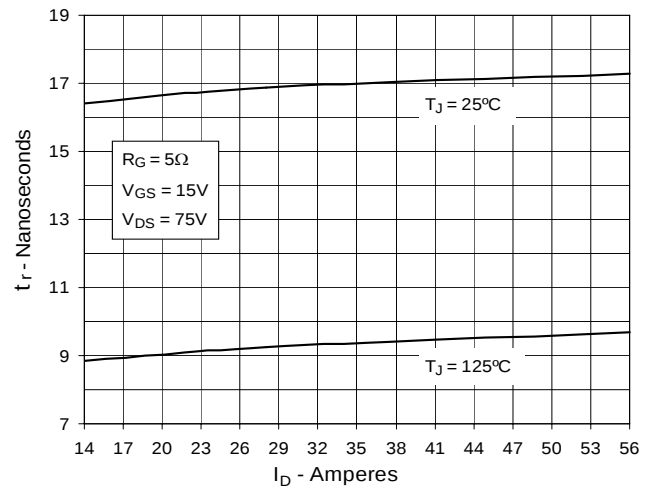


Fig. 15. Resistive Turn-on
Switching Times vs. Gate Resistance

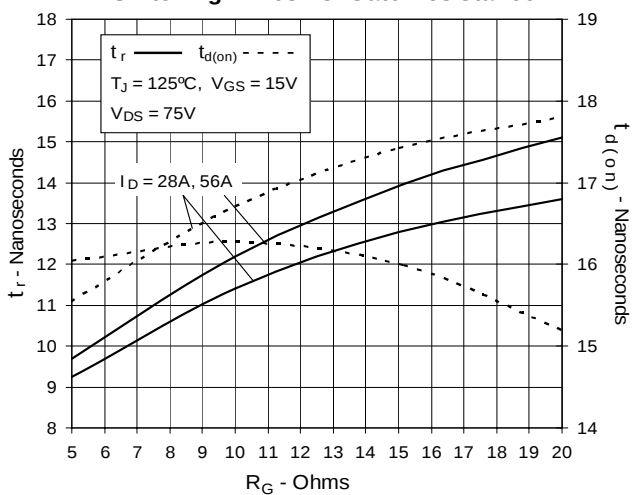


Fig. 16. Resistive Turn-off
Switching Times vs. Junction Temperature

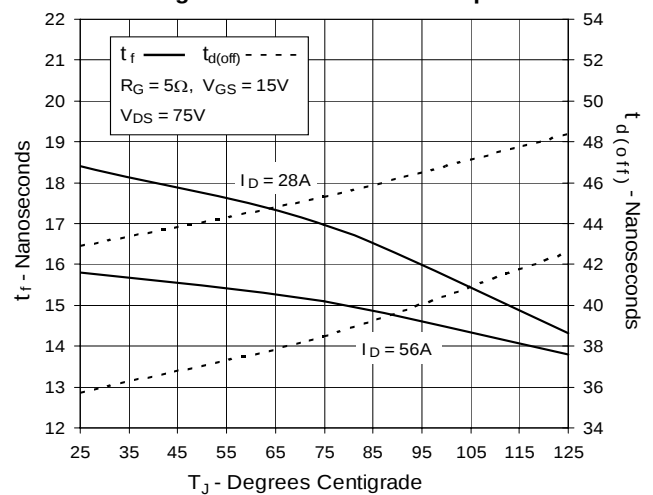


Fig. 17. Resistive Turn-off
Switching Times vs. Drain Current

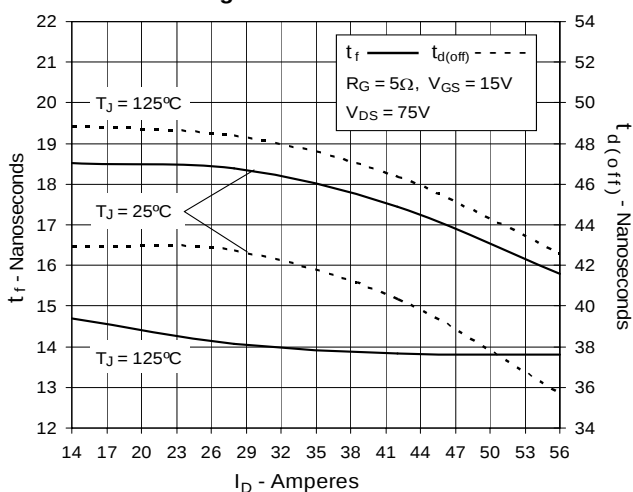


Fig. 18. Resistive Turn-off
Switching Times vs. Gate Resistance

